

METHOD OF FABRICATING TETRA-STATE MASK READ ONLY MEMORY**ABSTRACT OF THE DISCLOSURE**

A method of fabricating a tetra-state mask read only memory. A memory device is fabricated. Using a first photo-resist to dope the channel regions, a first coding step is performed to obtain a transistor having two different threshold voltage. Covering a gate oxide layer, and etching the first photo-resist layer to form a via, a buried bit line is formed. A poly-silicon layer is formed on the gate oxide layer. Doping the second poly-silicon layer by implanting ions to the source/drain regions, and using a second photo-resist layer, a second coding step is performed. An inverse transistor with two different threshold voltage is formed.

[Fig. 3]



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